

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

**Listing of Claims:**

Claim 1 (original): A manufacturing method of high purity copper sulfate, including the steps of dissolving copper sulfate crystals in purified water, performing evaporative concentration thereto, removing the crystals precipitated initially, performing further evaporative concentration to effect crystallization, subjecting this to filtration to obtain high purity copper sulfate, and performing desiccation thereto.

Claim 2 (original): A manufacturing method of high purity copper sulfate according to claim 1, wherein the initial pH of the solution in which the copper sulfate was dissolved in purified water is 2 to 4, and the pH of the solution after removing the crystals precipitated initially is 2 or less.

Claims 3-13 (canceled).

Claim 14 (new): A method according to claim 2, wherein 10wt% or more of the initial crystal is removed in relation to the initial input.

Claim 15 (new): A method according to claim 14, wherein the filtration solution after the final filtration is 2 to 40% of the original fluid volume.

Claim 16 (new): A method according to claim 15, wherein the desiccation temperature is 40 to 100°C.

Claim 17 (new): A method according to claim 1, wherein 10wt% or more of the initial crystal is removed in relation to the initial input.

Claim 18 (new): A method according to claim 1, wherein the filtration solution after the final filtration is 2 to 40% of the original fluid volume.

Claim 19 (new): A method according to claim 1, wherein the desiccation temperature is 40 to 100°C.

Claim 20 (new): A high purity copper sulfate prepared by a process comprising the steps of dissolving copper sulfate crystals in purified water, performing evaporative concentration thereto, removing the crystals precipitated initially, performing further evaporative concentration to effect crystallization, subjecting this to filtration to obtain high purity copper sulfate, and performing desiccation thereto, wherein a purity of said copper sulfate is 99.99wt% or higher and in which a content of transition metals, such as Fe, Cr, and Ni, is 3 wtppm or less.

Claim 21 (new): High purity copper sulfate according to claim 20, wherein a content of Ag and Cl in said copper sulfate is 1wtppm or less, respectively.

Claim 22 (new): High purity copper sulfate according to claim 21, wherein a content of alkali metals, such as Na and K, and alkaline earth metals, such as Ca and Mg, in said copper sulfate is 1 wtppm or less, respectively.

Claim 23 (new): High purity copper sulfate according to claim 22, wherein a content of an Si containing oxide in said copper sulfate is 10wtppm or less based on Si conversion.

Claim 24 (new): A copper sulfate having a purity of 99.99wt% or higher.

Claim 25 (new): A copper sulfate according to claim 24, wherein said copper sulfate has a content of transition metals, such as Fe, Cr, and Ni, of 3 wtppm or less.

Claim 26 (new): A copper sulfate according to claim 25, wherein said copper sulfate has a content of Ag and Cl of 1wtppm or less, respectively.

Claim 27 (new): A copper sulfate according to claim 26, wherein said copper sulfate has a content of alkali metals, such as Na and K, and alkaline earth metals, such as Ca and Mg, of 1 wtppm or less, respectively.

Claim 28 (new): A copper sulfate according to claim 27, wherein said copper sulfate has a content of an Si containing oxide of 10wtppm or less based on Si conversion.

Claim 29 (new): A copper sulfate according to claim 24, wherein said copper sulfate has a content of Ag and Cl of 1wtppm or less, respectively.

Claim 30 (new): A copper sulfate according to claim 24, wherein said copper sulfate has a content of alkali metals, such as Na and K, and alkaline earth metals, such as Ca and Mg, of 1 wtppm or less, respectively.

Claim 31 (new): A copper sulfate according to claim 24, wherein said copper sulfate has a content of an Si containing oxide of 10wtppm or less based on Si conversion.